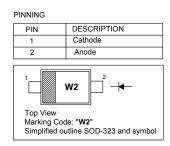
SILICON EPITAXIAL PLANAR SWITCHING DIODES



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	40	V
Reverse Voltage	V _R	40	V
Average Forward Current	I _{F(AV)}	200	mA
Peak Forward Current	I _{FM}	600	mA
Non-Repetitive Peak Forward Surge Current (t = 1 s)	I _{FSM}	1	А
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Characteristics at $T_a = 25 \ ^{\circ}C$

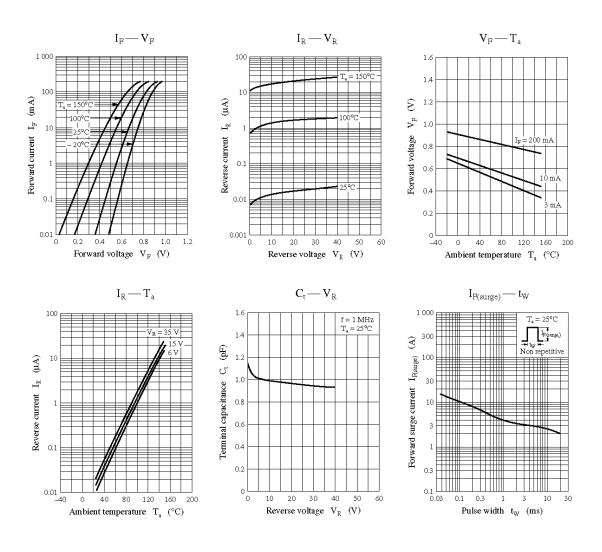
Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 200 mA	V _F	1.1	V
Reverse Current at V_R = 15 V at V_R = 35 V	I _R	50 500	nA
Total Capacitance at V _R = 0 V, f = 1 MHz	C _T	4	pF
Reverse Recovery Time at V _R = 6 V, I _F = 10 mA, I _{rr} = $0.1 \cdot I_R$, R _L = 100 Ω	t _{rr}	10	ns







Dated : 07/04/2009





SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)

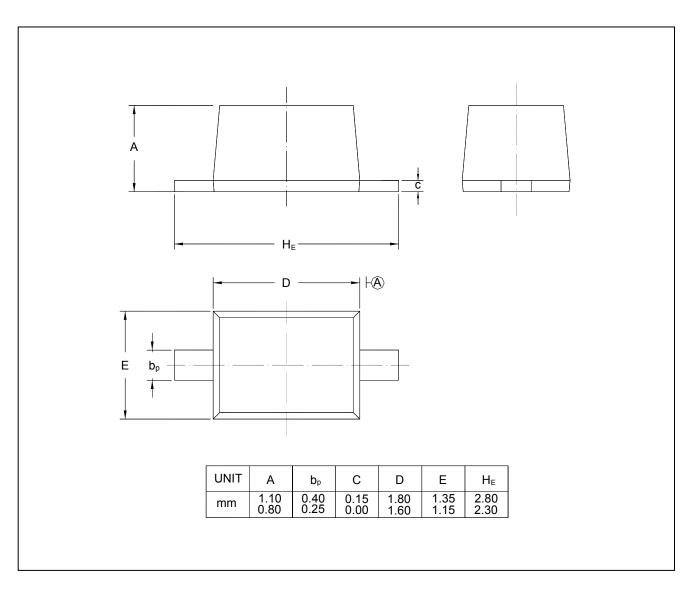


Dated : 07/04/2009

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323









Dated : 07/04/2009